REMARKS

Claim 1 has been amended. Claims 1 and 3 to 14 remain active in this application.

As astutely noted by the Examiner, the proposed revision to the specification and drawing was in error. Accordingly, a revised amendment to the specification and proposed drawing correction which is attached hereto are provided to more clearly set forth the method as originally disclosed and to replace to prior proposed amendment to the specification and drawings.. Figure 1E follows directly from Figure 1D since it is stated to be a part of the same process flow ("various stages of fabrication in accordance with one embodiment of the present invention") and therefore must conform to the step set forth through Figure 1D, which is now clearly the case. The term "source/drain" as applied to region 34 has been removed to avoid any confusion Approval is respectfully requested.

Claims 1 and 3 to 17 were rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. The application has been amended as noted above to overcome this rejection. With reference to the objection relative to the second doped region having a greater charge-carrier mobility, reference is directed to page 3, lines 14ff of the specification wherein it is stated:

"A technical advantage is that a subsurface channel layer is formed in the central portion of the channel that has greater charge-carrier mobility than conventional surface channels, thus allowing a lower dopant concentration to be used in the subsurface channel layer without negatively affecting transistor performance."(emphasis not in original). The subsurface layer is layer 26 and the surface layer would therefore be 28. It follows that the subsurface channel 26 is

stated to have a greater charge-carrier mobility than does the surface channel 28 since surface channel 28 is not stated to other than conventional.

The subsurface layer is stated to be the primary conduction channel at page 7, lines 3 to 7 where it is stated:

"Specifically, this transistor utilizes subsurface doped layer 26 as the primary conduction channel between source/drain regions 34. Subsurface doped layer 26 has greater charge-carrier mobility than conventional surface channels."

In addition, claim 1 has been amended to conform to the corrected specification. The other independent claims are believed to read on the corrected disclosure and do not require amendment.

Since none of the claims have been rejected on prior art, it is assumed that these claims should now be allowable in view of the arguments presented above with reference to the rejection under section 112, first paragraph.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,

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